Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|---------------------------------------|-------------------|------------------|
| Peak Repetitive Off–State Voltage Note 1 $(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ Sine Wave } 50 \text{ to } 60 \text{ Hz}, \text{Gate Open})$ | V _{DRM,} V _{RRM} | 400 600 800 | ٧ |
| Peak Gate Voltage (Pulse Width $\leq 1.0 \mu sec; T_C = 90^{\circ}C$) | V _{GM} | 10 | V |
| On-State Current RMS; Full Cycle Sine Wave 50 to 60 Hz (T _C = +90°C) | I _{T(RMS)} | 15 | Α |
| Circuit Fusing Consideration (t = 8.3 ms) | l ² t | 93 | A ² s |
| Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = +80°C) Preceded and Followed by Rated Current | I _{TSM} | 150 | Α |
| Peak Gate Power (T _C = +80°C, Pulse Width = 1.0 μs) | P _{GM} | 20 | W |
| Average Gate Power (T _C = +80°C, t = 8.3 ms) | P _{G(AV)} | 0.5 | W |
| Peak Gate Current (Pulse Width $\leq 1.0 \mu sec; T_C = 90^{\circ}C$) | I _{GM} | 2.0 | Α |
| Operating Junction Temperature Range | TJ | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



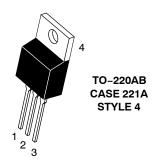
ON Semiconductor®

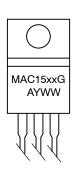
http://onsemi.com

TRIACS 15 AMPERES RMS 400 thru 800 VOLTS



MARKING DIAGRAM





MAC15xx = Specific Device Code xx = See Table on Page 2 A = Assembly Location Y = Year WW = Work Week

= Pb-Free Package

| PIN ASSIGNMENT | | | |
|----------------|-----------------|--|--|
| 1 | Main Terminal 1 | | |
| 2 | Main Terminal 2 | | |
| 3 | Gate | | |
| 4 | Main Terminal 2 | | |

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|----------------|-------|------|
| Thermal Resistance, Junction-to-Case | $R_{	heta JC}$ | 2.0 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{	heta JA}$ | 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | T _L | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

| Characteristic | | Symbol | Min | Тур | Max | Unit |
|--|---|---------------------------------------|------------------|--------------------------|----------------------|----------|
| OFF CHARACTERISTICS | | | • | | • | |
| Peak Blocking Current (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open) | T _J = 25°C T _J = 125°C | I _{DRM,} I _{RRM} | | - - | 10 2.0 | μA mA |
| ON CHARACTERISTICS | | | | I | | ı |
| Peak On-State Voltage Note 2 (I _{TM} = ±21 A Peak) | | V_{TM} | - | 1.3 | 1.6 | V |
| Gate Trigger Current (Continuous dc) (V_D = 12 Vdc, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY | | l _{GT} | - - - - | - - - - | 50 50 50 75 | mA |
| Gate Trigger Voltage (Continuous dc) (V_D = 12 Vdc, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY | | V _{GT} | - - - - | 0.9 0.9 1.1 1.4 | 2 2 2 2.5 | V |
| Gate Non–Trigger Voltage (V_D = 12 V, R_L = 100 Ω) T_J = 110°C) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY | | | 0.2 0.2 | - - | - - | V |
| Holding Current (V _D = 12 Vdc, Gate Open, Initiating Current = ±200 mA) | | | _ | 6.0 | 40 | mA |
| Turn-On Time (V_D = Rated V_{DRM} , I_{TM} = 17 A) (I_{GT} = 120 mA, Rise Time = 0.1 μ s, Pulse Width = 2 μ s) | | | - | 1.5 | - | μs |
| DYNAMIC CHARACTERISTICS | | | • | • | • | |
| Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = Commutating di/dt = 7.6 A/ms, Gate Unenergized, T_C = 80°C) | 21 A, | dv/dt(c) | - | 5.0 | - | V/μs |

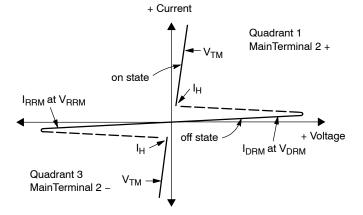
^{2.} Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

ORDERING INFORMATION

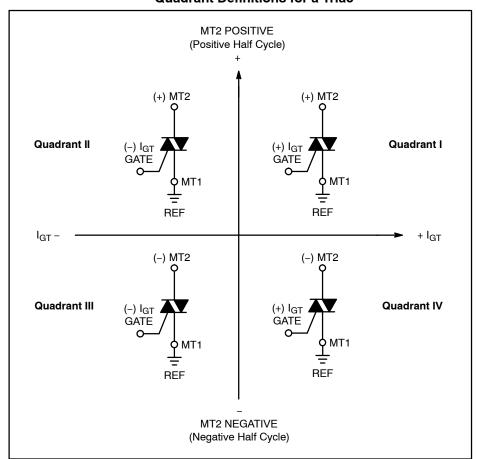
| Device | Device Marking | Package | Shipping |
|-----------|----------------|-----------------------|-----------------|
| MAC15-008 | | TO-220AB | |
| MAC15-8G | MAC15-8 | TO-220AB (Pb-Free) | |
| MAC15-10 | | TO-220AB | |
| MAC15-10G | MAC1510 | TO-220AB (Pb-Free) | |
| MAC15A6 | | TO-220AB | |
| MAC15A6G | MAC15A6 | TO-220AB (Pb-Free) | 500 Units Bulk |
| MAC15A8 | | TO-220AB | |
| MAC15A8G | MAC15A8 | TO-220AB (Pb-Free) | |
| MAC15A10 | | TO-220AB | |
| MAC15A10G | MAC15A10 | TO-220AB (Pb-Free) | |
| MAC15A10T | | TO-220AB | 50 Units / Rail |

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|------------------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I _{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I _H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

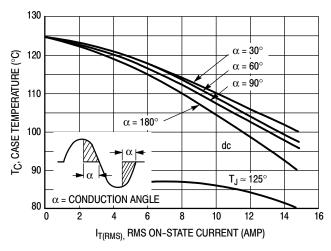


Figure 1. RMS Current Derating

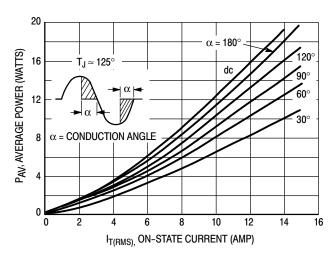


Figure 2. On-State Power Dissipation

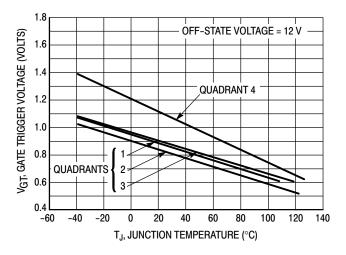


Figure 3. Typical Gate Trigger Voltage

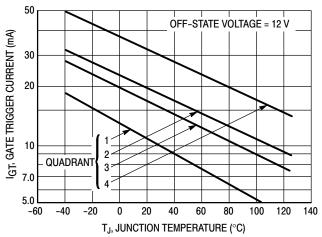
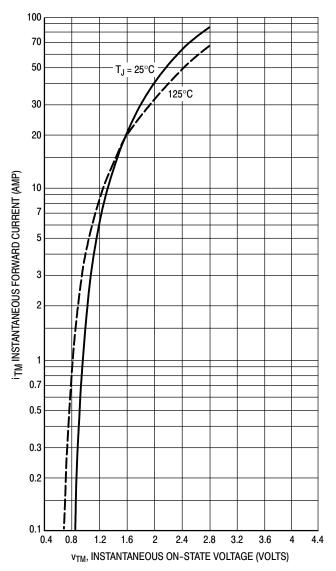


Figure 4. Typical Gate Trigger Current



20 GATE OPEN MAIN TERMINAL #1 **POSITIVE** IH, HOLDING CURRENT (mA) 10 7.0 5.0 MAIN TERMINAL #2 **POSITIVE** 3.0 2.0 -40 80 -60 -20 20 40 60 100 120 140 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. Typical Holding Current

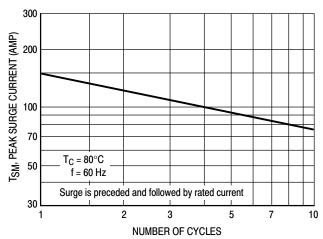


Figure 5. On-State Characteristics

Figure 7. Maximum Non-Repetitive Surge Current

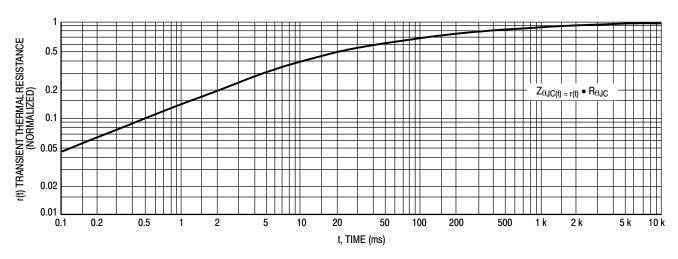
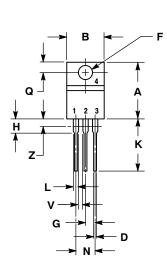
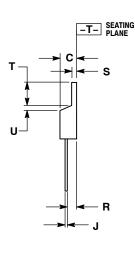


Figure 8. Thermal Response

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 **ISSUE O**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL
 BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIN | IETERS |
|-----|--------|---------|--------|--------|
| DIM | MIN | MIN MAX | | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

PIN 1. MAIN TERMINAL 1

MAIN TERMINAL 2 2.

GATE

MAIN TERMINAL 2

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered radiations of semiconduction Components industries, Ite (SCILLO). Solitude services are injust of make drainges without further induce to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative